

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-16 (Canceled)

17. (Currently Amended): Light emitting semiconductor body for use in an LED housing, said semiconductor body being provided with a layer comprising a wavelength-converting casting composition; and  
said casting composition ~~containing a transparent epoxy resin and~~ comprising luminous substance particles;  
said luminous substance particles comprising luminous substance pigments selected from the group consisting of garnets doped with ~~rear~~ rare earths; thiogallates doped with ~~rear~~ rare earths; aluminates doped with ~~rear~~ rare earths; and orthosilicates doped with ~~rear~~ rare earths; and  
said luminous substance pigments having grain sizes  $\leq 20 \mu\text{m}$  and a  $[[d_{50}]]$  mean grain diameter  $d_{50} \leq 5 \mu\text{m}$ .
18. (Previously Presented): Semiconductor body according to claim 17, wherein the luminous substance pigments are substantially spherical particles.
19. (Previously Presented): Semiconductor body according to claim 17, wherein the luminous substance pigments are substantially flakelike particles.

20. (Currently Amended): Semiconductor body according to claim 17, wherein the mean grain diameter  $d_{50}$  of said luminous substance pigments is between 1 and 2 micrometers.
21. (Previously Presented): Semiconductor body according to claim 17, wherein said luminous substance pigments contain Ce-doped garnet material.
22. (Previously Presented): Semiconductor body according to claim 17, wherein said luminous substance pigments contain YAG:Ce material.
23. (Currently Amended): Semiconductor body according to claim 17, wherein ~~the~~ an iron content in the casting composition is  $\leq 20$  ppm.
24. (Previously Presented): Semiconductor body according to claim 17, wherein the luminous substance pigments are provided with a silicone coating.
25. (Previously Presented): Semiconductor body according to claim 17, wherein said luminous substance pigments convert radiation from the ultraviolet, blue or green spectral range into light with a relatively longer wavelength.
26. (Previously Presented): Semiconductor body according to claim 17, wherein said layer containing light-scattering particles.
27. (Previously Presented): Semiconductor body according to claim 17, wherein said semiconductor body is adapted to emit radiation in a blue spectral range having a maximum luminescence intensity at a wavelength between 420 nm and 460 nm.
28. (Currently Amended): Light emitting semiconductor body for use in an LED housing,

said semiconductor body being provided with a layer comprising a wavelength-converting casting composition; and

said casting composition ~~containing a transparent epoxy resin and~~ comprising luminous substance particles;

said luminous substance particles comprising luminous substance pigments from Ce-doped phosphors; and

said luminous substance pigments having grain sizes  $\leq 20 \mu\text{m}$  and a  $[[d_{50}]]$  mean grain diameter  $d_{50} \leq 5 \mu\text{m}$ .

29. (Previously Presented): Semiconductor body according to claim 28, wherein the luminous substance pigments are substantially spherical particles.
30. (Previously Presented): Semiconductor body according to claim 28, wherein the luminous substance pigments are substantially flakelike particles.
31. (Currently Amended): Semiconductor body according to claim 28, wherein the  $[[d_{50}]]$  mean grain diameter  $d_{50}$  of said luminous substance pigments is between 1 and 2 micrometers.
32. (Currently Amended): Semiconductor body according to claim 28, wherein ~~the~~ an iron content in the casting composition is  $\leq 20$  ppm.
33. (Previously Presented): Semiconductor body according to claim 28, wherein the luminous substance pigments are provided with a silicone coating.
34. (Previously Presented): Semiconductor body according to claim 28, wherein said luminous substance pigments convert radiation from the ultraviolet, blue or green spectral range into light with a relatively longer wavelength.

35. (Previously Presented): Semiconductor body according to claim 28, wherein said layer containing light-scattering particles.
36. (Previously Presented): Semiconductor body according to claim 28, wherein said semiconductor body is adapted to emit radiation in a blue spectral range having a maximum luminescence intensity at a wavelength between 420 nm and 460 nm.
37. (New): Semiconductor body according to claim 17, wherein the casting composition further comprises a transparent resin.
38. (New): Semiconductor body according to claim 37, wherein the transparent resin is an epoxy resin.
39. (New): Semiconductor body according to claim 28, wherein the casting composition further comprises a transparent resin.
40. (New): Semiconductor body according to claim 39, wherein the transparent resin is an epoxy resin.